

## PATENT APPLICATION

# IN THE UNITED SENSES PATENT AND TRADEMARK OFFICE

In re the Application of

Kazuhiko OKAWA et al.

Group Art Unit: 2826

Application No.: 09/866,800

Examiner:

J. Mondt

Filed: May 30, 2001

Docket No.:

109657

For:

SEMICONDUCTOR DEVICE HAVING ELECTROSTATIC PROTECTION CIRCUIT

AND METHOD OF FABRICATING THE SAME

#### AMENDMENT UNDER 37 CFR §1.111

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

In reply to the Office Action mailed March 11, 2002, please amend the aboveidentified application as follows:

### IN THE CLAIMS:

Please add new claims 25 and 26 as follows:

- The semiconductor device according to claim 1, wherein the first diffusion region forms the drain of the MOS transistor .--
- The semiconductor device according to claim 20, wherein the first diffusion region forms the drain of the MOS transistor .--

#### **REMARKS**

Claims 1-26 are pending in this application. Claims 8-19 and 24 have previously been withdrawn from consideration. By this Amendment, claims 25 and 26 are added. No new matter is added.

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